

# MOSFET – Power, Single, N-Channel, TOLL

80 V, 1.05 mΩ, 351 A

## NTBLS1D1N08H

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- Lowers Switching Noise/EMI
- These Devices are Pb-Free and are RoHS Compliant

### Typical Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                                                      | Symbol         | Value                                          | Unit             |
|--------------------------------------------------------------------------------|----------------|------------------------------------------------|------------------|
| Drain-to-Source Voltage                                                        | $V_{DSS}$      | 80                                             | V                |
| Gate-to-Source Voltage                                                         | $V_{GS}$       | $\pm 20$                                       | V                |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)                          | $I_D$          | $T_C = 25^\circ\text{C}$                       | A                |
|                                                                                |                | $T_C = 100^\circ\text{C}$                      |                  |
| Power Dissipation $R_{\theta JC}$ (Note 1)                                     | $P_D$          | $T_C = 25^\circ\text{C}$                       | W                |
|                                                                                |                | $T_C = 100^\circ\text{C}$                      |                  |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)                       | $I_D$          | $T_A = 25^\circ\text{C}$                       | A                |
|                                                                                |                | $T_A = 100^\circ\text{C}$                      |                  |
| Power Dissipation $R_{\theta JA}$ (Notes 1, 2)                                 | $P_D$          | $T_A = 25^\circ\text{C}$                       | W                |
|                                                                                |                | $T_A = 100^\circ\text{C}$                      |                  |
| Pulsed Drain Current                                                           | $I_{DM}$       | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | A                |
| Operating Junction and Storage Temperature Range                               | $T_J, T_{stg}$ | $-55$ to $+175$                                | $^\circ\text{C}$ |
| Source Current (Body Diode)                                                    | $I_S$          | 259                                            | A                |
| Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 31.9 \text{ A}$ ) | $E_{AS}$       | 1580                                           | mJ               |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)              | $T_L$          | 260                                            | $^\circ\text{C}$ |

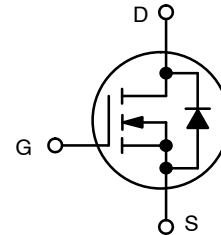
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter                                   | Symbol          | Value | Unit               |
|---------------------------------------------|-----------------|-------|--------------------|
| Junction-to-Case – Steady State             | $R_{\theta JC}$ | 0.48  | $^\circ\text{C/W}$ |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 35.8  |                    |

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 80 V          | 1.05 mΩ @ 10 V           | 351 A             |

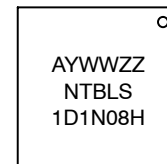


N-CHANNEL MOSFET



TOLL  
CASE 100CU

### MARKING DIAGRAM



NTBLS1D1N08H = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NTBLS1D1N08H

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                           |                   |                                                     |                                    |    |    |     |               |
|-----------------------------------------------------------|-------------------|-----------------------------------------------------|------------------------------------|----|----|-----|---------------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ |                                    | 80 | –  | –   | V             |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ |                                                     |                                    | –  | 57 | –   | mV/°C         |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$         | $T_J = 25\text{ }^{\circ}\text{C}$ | –  | –  | 10  | $\mu\text{A}$ |
|                                                           |                   |                                                     | $T_J = 125^{\circ}\text{C}$        | –  | –  | 250 |               |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$         |                                    | –  | –  | 100 | nA            |

### ON CHARACTERISTICS (Note 4)

|                                   |                  |                                                 |     |      |      |                      |
|-----------------------------------|------------------|-------------------------------------------------|-----|------|------|----------------------|
| Gate Threshold Voltage            | $V_{GS(TH)}$     | $V_{GS} = V_{DS}, I_D = 650\text{ }\mu\text{A}$ | 2.0 | 2.9  | 4.0  | V                    |
| Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ |                                                 | –   | –7.7 | –    | mV/ $^\circ\text{C}$ |
| Drain-to-Source On Resistance     | $R_{DS(on)}$     | $V_{GS} = 10\text{ V}, I_D = 50\text{ A}$       | –   | 0.92 | 1.05 | m $\Omega$           |
| Forward Transconductance          | $g_{FS}$         | $V_{DS} = 5\text{ V}, I_D = 50\text{ A}$        | –   | 213  | –    | S                    |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |              |                                                                 |   |       |   |    |
|------------------------------|--------------|-----------------------------------------------------------------|---|-------|---|----|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 40\text{ V}$   | – | 11200 | – | pF |
| Output Capacitance           | $C_{OSS}$    |                                                                 | – | 1600  | – |    |
| Reverse Transfer Capacitance | $C_{RSS}$    |                                                                 | – | 49    | – |    |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 64\text{ V}, I_D = 50\text{ A}$ | – | 166   | – | nC |
| Threshold Gate Charge        | $Q_{G(TH)}$  |                                                                 | – | 29    | – |    |
| Gate-to-Source Charge        | $Q_{GS}$     |                                                                 | – | 44    | – |    |
| Gate-to-Drain Charge         | $Q_{GD}$     |                                                                 | – | 35    | – |    |
| Plateau Voltage              | $V_{GP}$     |                                                                 | – | 4     | – |    |

### SWITCHING CHARACTERISTICS (Note 5)

|                     |              |                                                                                        |   |     |   |    |
|---------------------|--------------|----------------------------------------------------------------------------------------|---|-----|---|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 64\text{ V}, I_D = 50\text{ A}, R_G = 6\text{ }\Omega$ | – | 45  | – | ns |
| Rise Time           | $t_r$        |                                                                                        | – | 43  | – |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                        | – | 141 | – |    |
| Fall Time           | $t_f$        |                                                                                        | – | 43  | – |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |          |                                                                              |                           |   |      |     |    |
|-------------------------|----------|------------------------------------------------------------------------------|---------------------------|---|------|-----|----|
| Forward Diode Voltage   | $V_{SD}$ | $V_{GS} = 0\text{ V}, I_S = 50\text{ A}$                                     | $T_J = 25^\circ\text{C}$  | – | 0.76 | 1.2 | V  |
|                         |          |                                                                              | $T_J = 125^\circ\text{C}$ | – | 0.6  | –   |    |
| Reverse Recovery Time   | $t_{RR}$ | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 50\text{ A}$ |                           | – | 92   | –   | ns |
| Reverse Recovery Charge | $Q_{RR}$ |                                                                              |                           | – | 234  | –   | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

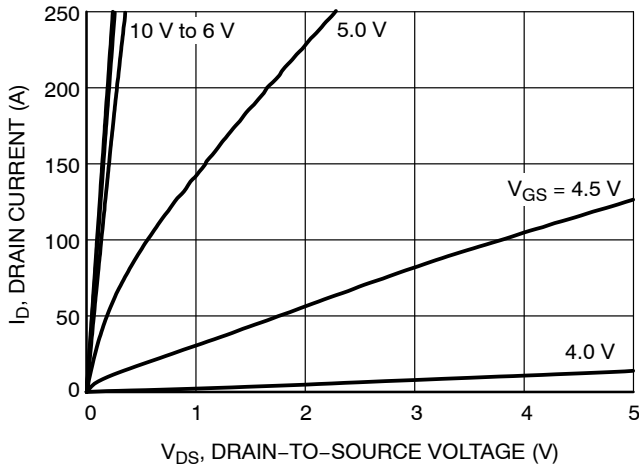


Figure 1. On-Region Characteristics

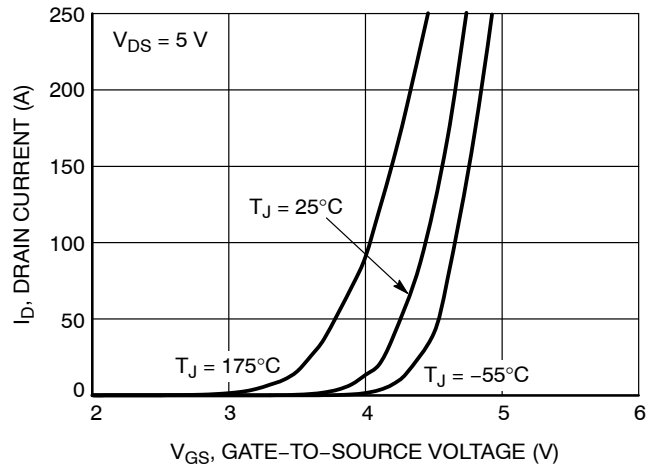


Figure 2. Transfer Characteristics

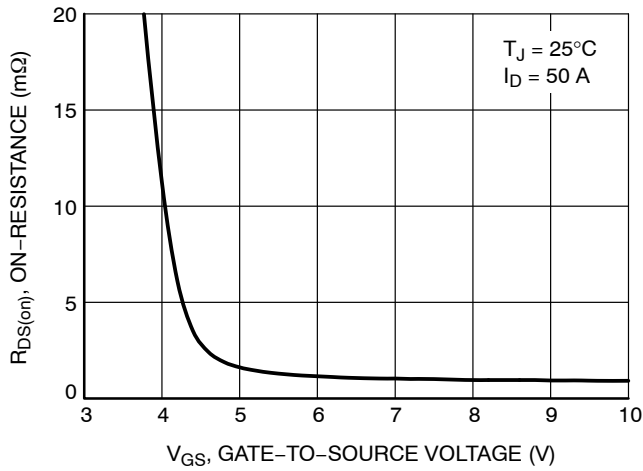


Figure 3. On-Resistance vs. Gate-to-Source Voltage

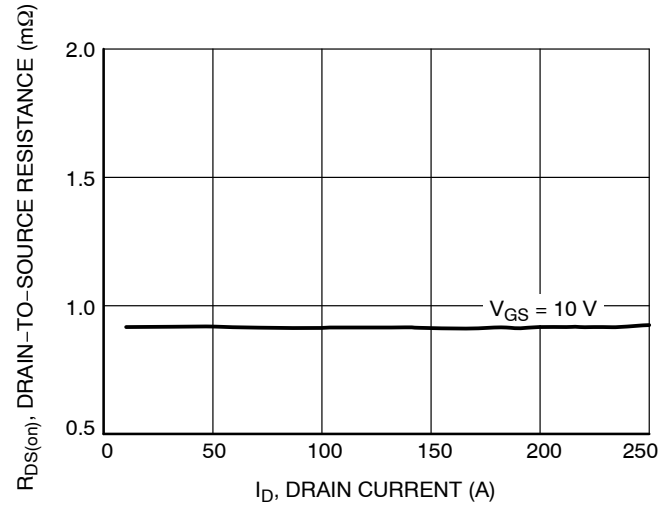


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

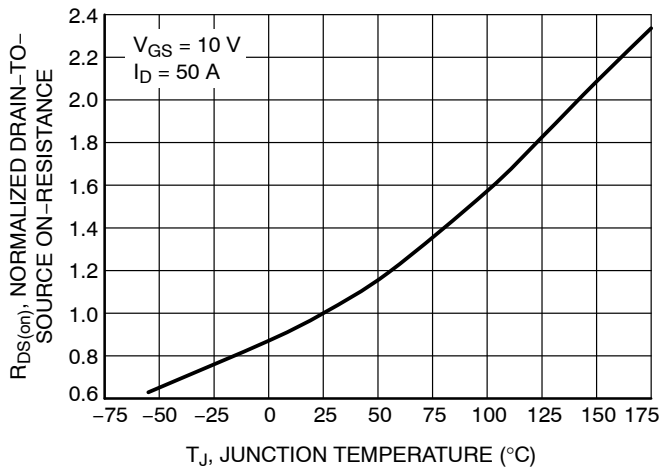


Figure 5. On-Resistance Variation with Temperature

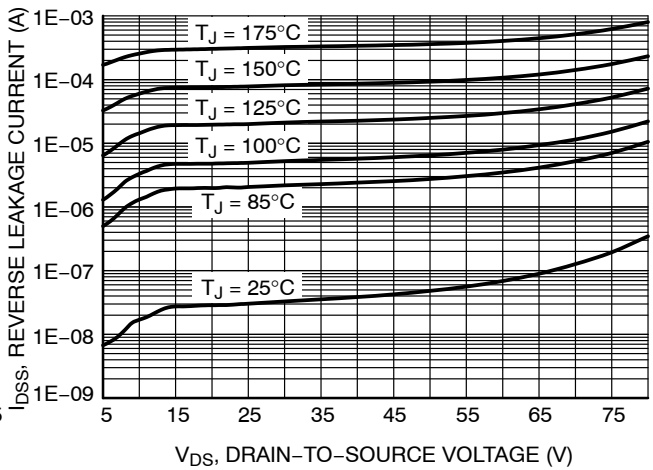


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

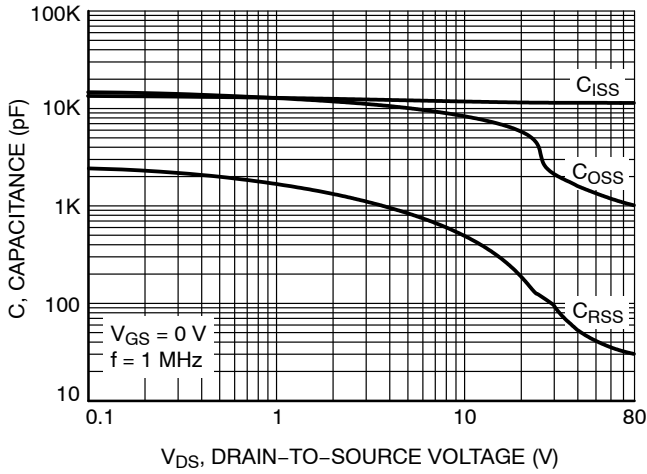


Figure 7. Capacitance Variation

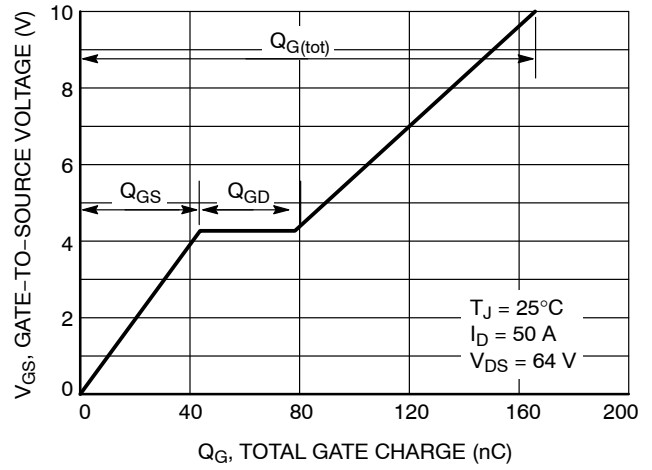


Figure 8. Gate-to-Source Voltage vs. Total Charge

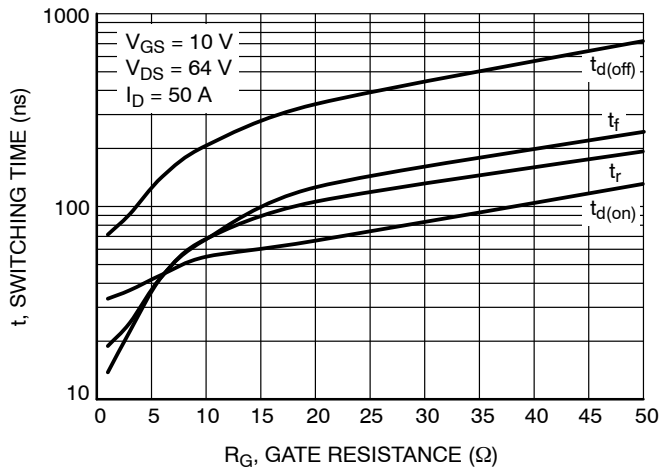


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

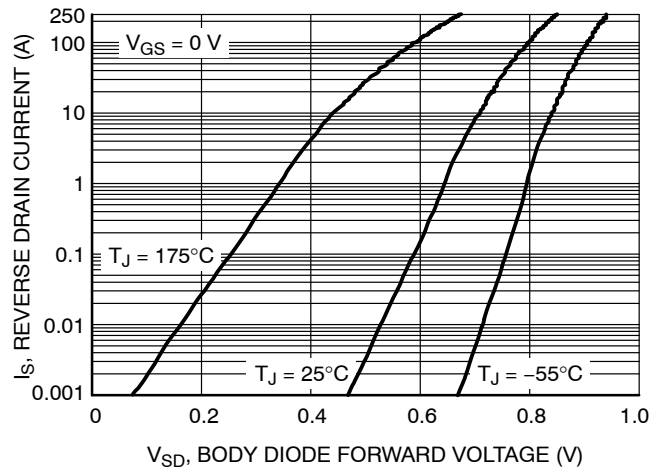


Figure 10. Diode Forward Voltage vs. Current

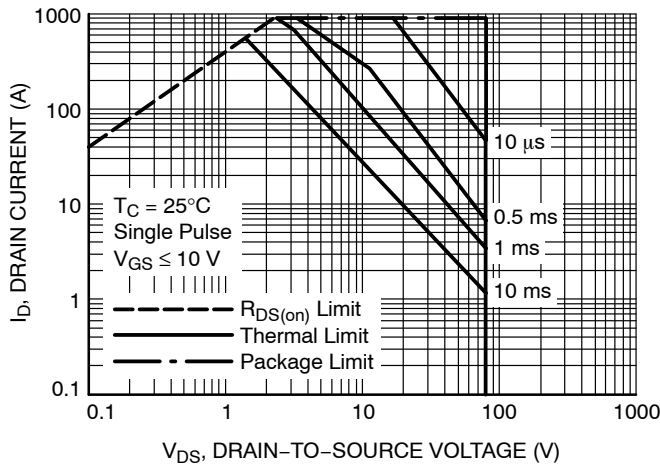


Figure 11. Maximum Rated Forward Biased Safe Operating Area

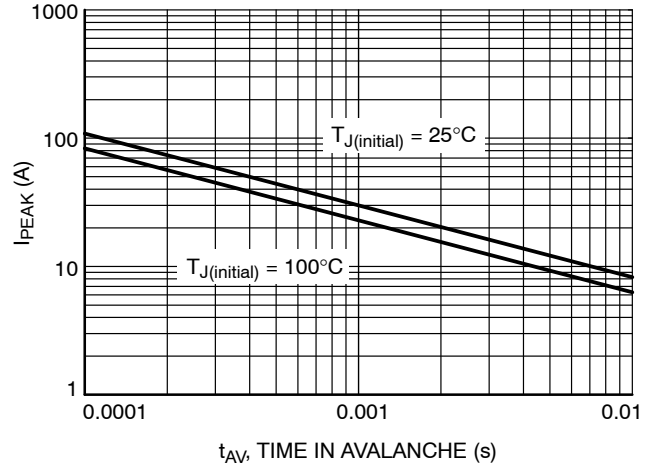


Figure 12. Maximum Drain Current vs. Time in Avalanche

# NTBLS1D1N08H

## TYPICAL CHARACTERISTICS

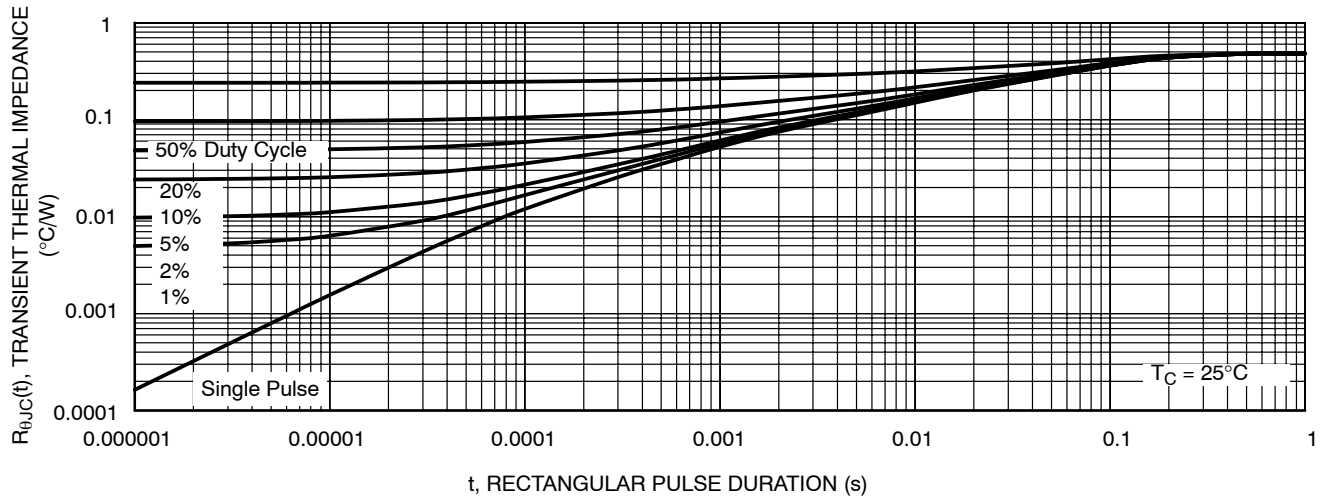


Figure 13. Thermal Response

### DEVICE ORDERING INFORMATION

| Device       | Marking          | Package              | Shipping <sup>†</sup> |
|--------------|------------------|----------------------|-----------------------|
| NTBLS1D1N08H | NTBLS<br>1D1N08H | M0-299A<br>(Pb-Free) | 2000 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).



H-PSOF8L 11.68x9.80x2.30, 1.20P  
CASE 100CU  
ISSUE F

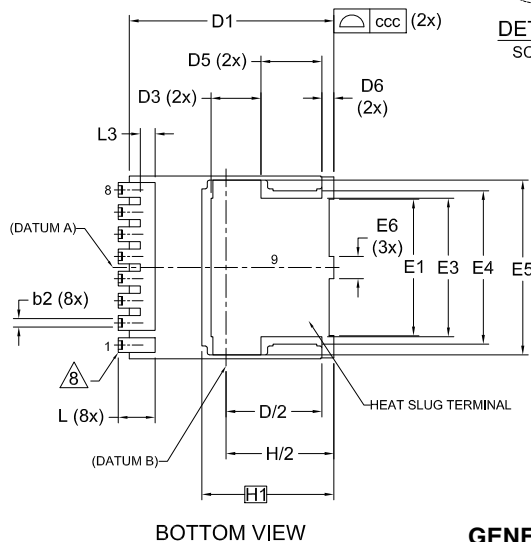
DATE 30 JUL 2024



\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

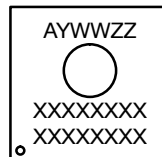


- NOTES:
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
  2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
  3. "e" REPRESENTS THE TERMINAL PITCH.
  4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g., EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
  5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
  6. DIMENSIONS b1, L1, L2 APPLY TO PLATED TERMINALS.
  7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
  8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.



GENERIC  
MARKING DIAGRAM\*

A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Assembly Lot Code  
XXXX = Specific Device Code



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| DIM | MILLIMETERS |       |       |
|-----|-------------|-------|-------|
|     | MIN.        | NOM.  | MAX.  |
| A   | 2.20        | 2.30  | 2.40  |
| A1  | 1.70        | 1.80  | 1.90  |
| b   | 0.70        | 0.80  | 0.90  |
| b1  | 9.70        | 9.80  | 9.90  |
| b2  | 0.35        | 0.45  | 0.55  |
| c   | 0.40        | 0.50  | 0.60  |
| D   | 10.28       | 10.38 | 10.48 |
| D/2 | 5.09        | 5.19  | 5.29  |
| D1  | 10.98       | 11.08 | 11.18 |
| D2  | 3.20        | 3.30  | 3.40  |
| D3  | 2.60        | 2.70  | 2.80  |
| D4  | 4.45        | 4.55  | 4.65  |
| D5  | 3.20        | 3.30  | 3.40  |
| D6  | 0.55        | 0.65  | 0.75  |
| E   | 9.80        | 9.90  | 10.00 |
| E1  | 7.30        | 7.40  | 7.50  |
| E2  | 0.30        | 0.40  | 0.50  |
| E3  | 7.40        | 7.50  | 7.60  |
| E4  | 8.20        | 8.30  | 8.40  |

| DIM | MILLIMETERS |       |       |
|-----|-------------|-------|-------|
|     | MIN.        | NOM.  | MAX.  |
| E5  | 9.36        | 9.46  | 9.56  |
| E6  | 1.10        | 1.20  | 1.30  |
| E7  | 0.15        | 0.18  | 0.21  |
| e   | 1.20 BSC    |       |       |
| e/2 | 0.60 BSC    |       |       |
| H   | 11.58       | 11.68 | 11.78 |
| H/2 | 5.74        | 5.84  | 5.94  |
| H1  | 7.15 BSC    |       |       |
| L   | 1.90        | 2.00  | 2.10  |
| L1  | 0.60        | 0.70  | 0.80  |
| L2  | 0.50        | 0.60  | 0.70  |
| L3  | 0.70        | 0.80  | 0.90  |
| Θ   | 10° REF     |       |       |
| Θ1  | 10° REF     |       |       |
| aaa | 0.20        |       |       |
| bbb | 0.25        |       |       |
| ccc | 0.20        |       |       |
| ddd | 0.20        |       |       |
| eee | 0.10        |       |       |

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